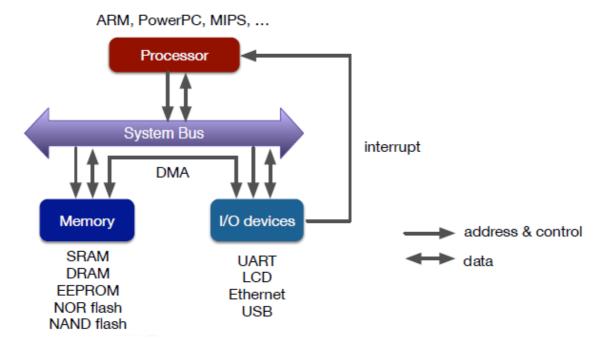
# **Memory Systems**

#### **Embedded HW Structure**



#### Role

- Workspace for computer programs
- Permanent storage for programs and data

## **Abstraction of memory**

- Virtually **flat** memory space
  - A single **logical address space** from an application perspective
  - Assume an ideal memory: read/write any location in 1 CPU clock

## **Implementation**

- Impossible to implement using a single type of memory device
- A well-implemented "Memory Hierarchy"
- Composed of a set of memory subsystems
  - o Caches, DRAMs, disks, tapes, distribtued file systems, etc.

#### Goal

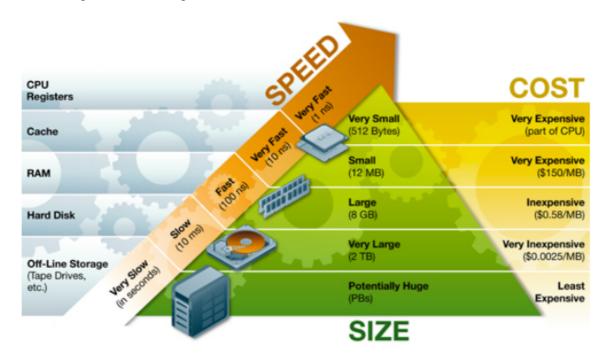
- Simultaneously achieve speed & capacity
  - Speed: to provide toe performance of the fastest component
  - o Capacity: At a cost of the cheapest component

# **Locality of reference**

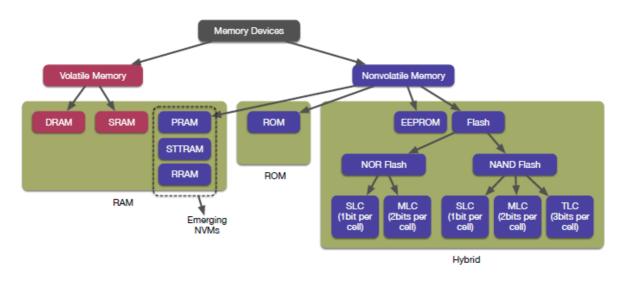
• The key to memory hierarchy design

Temporal Locality	Spatial Locality
	If one memory location is referenced, its neighbor will be highly likely to be referenced in the near future.

## **Memory Hierarchy**



# **Memory Taxonomy**



### **SRAM(Static RAM)**

- 4T or 6T Strutcure (T = Transistor)
- Volatile: Data is lost when not powered
- Stable: Holds value as long as power applied
- Very fast (~tens of ns): Suitable for L1 and L2 caches
- Very **expensive**: Typical size range: tens of Kbits ~ several Mbits

#### DRAM(Dynamic RAM)

- 1T1C Structure (C = Capacitor): The charge gradually leaks off
- Volatile: Data is lost when not powered
- **Unstable**: Data is lost without a periodic refresh
- Destructive read (charge consumed by read): Must rewrite after read
- Fast (~hundreds of ns): Suitable for main memory
- Very **Expensive**: Typical size range: several **Gbits**

#### **Flash Memory**

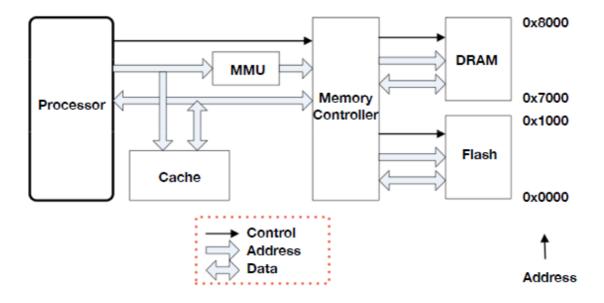
- Operation principle
  - Electrons trapped in the floating gate
- Nonvolatile
  - Electrons remain without power supply
  - Can be removed when high voltage supplied(erase operation)
- Read/Write(Program) Unit
  - Page (1KB ~ 4KB)
- Erase Unit: Block tens of pages
- Out-place update
  - o Erase-before write constraint
  - o Requires garbage collection

#### Multi-Level Cell Flash

- Store two or more bits per cell
  - Fine-grained control of the amount of charge to be stored
- Features
  - Lower cost-per-bit
  - Slower program speed
  - Slower read speed
  - Decreased write endurance
  - Decreased data retention time



### **Memory System Structure**



# I/O Systems